

# OpAmp Corretional ITopobojes 

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## Uncompensated CMOS Operational Amplifier



$$
\mathrm{M} 1=\mathrm{M} 2 ; \mathrm{M} 3=\mathrm{M} 4
$$

Ignoring zeros we can model this topology as:

$A_{V 1}(0) \cong \frac{g_{m 1}}{g_{o 1}+g_{o 3}} \quad ; \quad A_{V 2}(0)=\frac{-g_{m 6}}{g_{o 6}+g_{o 7}} \quad ; \quad \omega_{p 1}=\frac{g_{o 2}+g_{04}}{C_{p 1}} ; \quad \omega_{p 2}=\frac{g_{o 6}+g_{o 7}}{C_{p 2}}$
$A_{V T}(s) \cong \frac{A_{V 1}(0) A_{V 2}(0) A_{V 3}(0)}{\left(1+s / \omega_{p 1}\right)\left(1+s / \omega_{p 2}\right)\left(1+s / \omega_{p 3}\right)} ; \quad \omega_{p 3} \cong \frac{g_{m 8}}{C_{L}}$

- The low frequency voltage gain is high enough for a number of applications.
- The open loop poles are far from the origin, this can cause stability problems for closed loop applications.
- Closed loop poles might end very close to the jw axis and some in the RHP.
- How to tackle this stability problem will be discussed next.


## Two-Stage Uncompensated Amplifier



Uncompensated Operational Amplifier
$-A_{V}=A_{V 1} A_{V 2}=\frac{g_{m 2}}{g_{02}+g_{04}} \frac{g_{m 6}}{g_{06}+g_{07}}$
Large voltage gain

- Poles are close to the $j \omega$ axis causing stability problems
$\because$

Employing a simple capacitor will split correctly the poles but will generate a Zero in the RHP.

Using an RC compensation can eliminate the zero and split poles. The resistor can be implemented with transistor in the ohmic region.


Improved internally compensated CMOS operational amplifier. Better bias for the output stage (M8 and M9)

A variation at the output stage with class - AB is shown below.


CMOS op-amp with class-AB output stage and RC pole splitting.
"Pole Splitting" can be carried out with a compensation capacitor feedback and a voltage buffer as shown below


Two-Stage amplifier with source follower compensation scheme

- Without M12 and M11 a zero in the PRH
- With buffer (voltage follower), zero is eliminated and pole sp $\because$ (due to $\mathrm{C}_{\mathrm{C}}$ ) is kept.



# An Improved Frequency Compensation Technique for CMOS Operational Amplifiers using Current Buffers 

## Background.-

## Two-Stage Op-amp with Miller compensation

- The first stage is a differential-input/single-ended output stage, and the second stage is a class $A$ or class $A B$ inverting output stage.

- DC Gain
$A_{v, 0}=-A_{v 1} A_{v 2}$
$A_{v 1}=g_{m 1} r_{o 1}$
$A_{v 2}=g_{m 2} r_{o 2}$
- Transfer Function
- Pole/zero locatpons $=\frac{1-\frac{c_{c}}{g_{m 2}} s}{1+\left(r_{o 1} C_{p}+A_{v 2} r_{o 1} C_{c}+r_{o 2} C_{L}\right) s+r_{01} r_{o 2}\left(C_{p} C_{c}+C_{p} C_{L}+C_{c} C_{L}\right) s^{2}}$

$$
\begin{array}{ll}
s_{z}=\frac{g_{m 2}}{C_{c}} & \text { RHP zero } \\
s_{p 1}=-\frac{1}{r_{o 1} C_{p}+A_{v 2} r_{o 1} C_{c}+r_{o 2} C_{L}} \approx-\frac{1}{A_{v 2} r_{o 1} C_{c}} & \text { Dominant Pole } \\
s_{p 2}=-\frac{r_{01} C_{p}+A_{v 2} r_{o 1} C_{c}+r_{o 2} C_{L}}{r_{o 1} r_{o 2}\left(C_{p} C_{c}+C_{p} C_{L}+C_{c} C_{L}\right)} \approx-\frac{g_{m 2}}{C_{L}} & \text { Non-dominant Pole }
\end{array}
$$

## Two-Stage Op-amp with Miller compensation

- Pole Splitting

- Pole/zero locations

$$
\begin{aligned}
& s_{z}=\frac{g_{m 2}}{C_{c}} \\
& s_{p 1}=-\frac{1}{A_{v 2} r_{o 1} C_{c}} \\
& s_{p 2}=-\frac{g_{m 2}}{C_{L}}
\end{aligned}
$$

- Pole-zero position diagram


Increasing $\mathrm{C}_{\mathrm{c}}$ achieves sufficient pole-splitting thus improving the PM. However, the larger $\mathrm{C}_{\mathrm{c}}$ shifts the RHP zero to lower frequencies thus ruining the PM.

## Miller Op-amp with Nulling Resistance

- Introducing a small series resistance in series with $\mathrm{C}_{\mathrm{c}}$ may cancel the RHP zero or shift it to the LHP.


$$
\begin{aligned}
& R_{c}=1 / g_{m 2} \\
& R_{c}>1 / g_{m 2}
\end{aligned}
$$

No zero
LHP zero - Can be used to cancel the first non-dominant pole.

- Disadvantages:
- To achieve a sufficient phase margin, second pole cross-over of the unity gain frequency should be avoided.

$$
f_{p 2} \gg G B W \quad \rightarrow \quad C_{L} \ll \frac{g_{m 2}}{g_{m 1}} C_{c}
$$

Thus, the Op-amp stability is severely degraded for capacitive loads of the same order as compensation capacitor.

## Improved compensation technique

- The RHP zero is a result of the feed-forward path through $\mathbf{C}_{\mathrm{c}}$.

- The RHP zero can be eliminated if we cut the feed-forward path and make the compensation capacitor unidirectional.


An Improved Frequency Compensation Technique for CMOS Operational Amplifiers

## Improved compensation technique

- The controlled current source injects AC current of $C_{c} \frac{d V_{o u t}}{d t}$ to the output of the first stage.

- DC Gain
$A_{v, 0}=-A_{v 1} A_{v 2}$
$A_{v 1}=g_{m 1} r_{o 1}$
$A_{v 2}=g_{m 2} r_{o 2}$
- Transfer Function

$$
A_{v}=\frac{A_{v, 0}}{1+\left(r_{o 1} C_{p}+A_{v 2} r_{o 1} C_{c}+r_{o 2}\left(C_{C}+C_{L}\right)\right) s+r_{o 1} r_{o 2} C_{p}\left(C_{C}+C_{L}\right) s^{2}}
$$

- Pole/zero locations

$$
\begin{array}{ll}
s_{p 1}=-\frac{1}{r_{o 1} C_{p}+A_{v 2} r_{o 1} C_{c}+r_{o 2}\left(C_{C}+C_{L}\right)} \approx-\frac{1}{A_{v 2} r_{o 1} C_{c}} & \text { Dominant Pole } \\
s_{p 2}=-\frac{r_{o 1} C_{p}+A_{v 2} r_{o 1} C_{c}+r_{o 2}\left(C_{C}+C_{L}\right)}{r_{01} r_{o 2} C_{p}\left(C_{C}+C_{L}\right)} \approx-\frac{g_{m 2} C_{c}}{C_{p}\left(C_{C}+C_{L}\right)} & \text { Non-dominant Pole }
\end{array}
$$

- To achieve sufficient PM

$$
f_{p 2} \gg G B W \quad \rightarrow \quad C_{L} \ll \frac{g_{m 2}}{g_{m 1}} \frac{C_{c}^{2}}{C_{p}}
$$

## Improved compensation technique

- Numerical example

Miller compensation with nulling resistance

## Dominant pole

$$
\omega_{d}=\frac{1}{g_{m 2} r_{01} r_{o 2} c_{c}}
$$

Non-dominant pole

$$
\omega_{n d}=\frac{g_{m 2}}{C_{L}}
$$

Gain-bandwidth product

$$
G B W=\frac{g_{m 1}}{c_{c}}
$$

Phase margin

$$
P M=90-\tan ^{-1}\left(\frac{G B W}{\omega_{n d}}\right)
$$

Improved compensation technique

Dominant pole

$$
\omega_{d}=\frac{1}{g_{m 2} r_{o 1} r_{o 2} c_{c}}
$$

Non-dominant pole

$$
\omega_{n d}=\frac{g_{m_{2}} C_{c}}{C_{p}\left(C_{c}+C_{L}\right)}
$$

Gain-bandwidth product

$$
G B W=\frac{g_{m 1}}{c_{c}}
$$

Phase margin

$$
P M=90-\tan ^{-1}\left(\frac{G B W}{\omega_{n d}}\right)
$$

- If $\frac{g_{m 2}}{g_{m 1}}=10, C_{C}=5 p F, C_{p}=0.5 p F$, and $\frac{\omega_{n d}}{G B W} \geq 4$ for $P M>75^{\circ}$

$$
C_{L} \leq \frac{G B W}{\omega_{n d}} \frac{g_{m 2}}{g_{m 1}} C_{c} \rightarrow C_{L} \leq 12.5 p F \quad C_{L} \leq \frac{G B W}{\omega_{n d}} \frac{g_{m 2}}{g_{m 1}} \frac{C_{c}^{2}}{C_{p}} \rightarrow C_{L} \leq 125 p F
$$

- The improved technique offers an order of magnitude improvement in capacitive load capability for the same performance.

Circuit Implementation

- Miller compensation with nulling resistance.

- Improved compensation technique.


Other performance parameters- PSR
Miller compensation with nulling resistance.

$\frac{V_{\text {OUT }}}{V_{S S}}=\frac{1+s A_{v 2} c_{c} r_{o 1}}{g_{m 1} g_{m 2} r_{o 1} r_{o 2}}$


- Improved compensation technique.


$$
\frac{V_{O U T}}{V_{S S}}=\frac{1+s C_{p} r_{o 1}}{g_{m 1} g_{m 2} r_{o 1} r_{o 2}\left(1+\frac{s}{G B W}\right)}
$$



## Design Example - Miller Compensation

- Design an OTA with $G B W>5 M H z, C_{L}=10 p F, P M>70$, and $S R>2$

V/ $\mu \mathrm{s}$.


$$
\begin{aligned}
& \text { - Choose } \mathrm{C}_{\mathrm{c}}=\mathrm{C}_{\mathrm{L}} / 2=5 \mathrm{pF} \text {. } \\
& \text { - } \quad \mathrm{GBW}>5 \mathrm{MHz} \\
& G B W=\frac{g_{m 1}}{c_{c}} \rightarrow g_{m 1} \geq 157 \mu S \\
& \text { - } \quad S R>2 V / \mu S \\
& S R=\frac{I_{p, 0}}{c_{c}} \rightarrow \quad I_{p, 0} \geq 20 \mu A \\
& \mathrm{PM}>70^{\circ} \\
& P M=90-\tan ^{-1}\left(\frac{G B W}{\omega_{n d}}\right) \rightarrow \omega_{n d} \geq 2.7 G B \\
& \text { Let } \\
& \omega_{n d}=3 \times G B W=\frac{g_{m 2}}{C_{L}} \rightarrow \frac{g_{m 2}}{g_{m 1}}=3 \frac{C_{L}}{C_{c}}=6 \\
& \text { Then } \\
& g_{m 2}=6 g_{m 1} \cong 1 \mathrm{mS} \rightarrow I_{p, 2}=3 I_{p, 0} \\
& \text { - Choose } R_{c}>1 / g_{m 2} \\
& R_{c} \geq 1 K \Omega
\end{aligned}
$$

## Design Example - Miller Compensation



## Design Example - Miller Compensation

- Capacitive load driving capability

- $\quad \mathrm{PM}>70^{\circ}$ for $\mathrm{C}_{\mathrm{L}}<15 \mathrm{pF}$.


## Design Example - Improved Compensation

- Design an OTA with $G B W>5 M H z, C_{L}=10 p F, P M>70$, and $S R>2$

V/us.


- Choose $\mathrm{C}_{\mathrm{c}}=\mathrm{C}_{\mathrm{L}} / 2=5 \mathrm{pF}$.
- $\mathrm{GBW}>5 \mathrm{MHz}$

$$
\begin{aligned}
& G B W=\frac{g_{m 1}}{G_{1}} \rightarrow g_{m 1} \geq 157 \mu \mathrm{~S} \\
& \mathrm{SR}>2 \mathrm{~V} / \mu \mathrm{S} \\
& S R=\frac{I_{p, 0}}{C_{c}} \rightarrow I_{p, 0} \geq 20 \mu \mathrm{~A}
\end{aligned}
$$

In order to ${ }_{\text {frame }}$ the current transformer biased during slewing interval

$$
\begin{aligned}
& I_{p 3}>I_{p 0} \quad \rightarrow \quad I_{p, 3}=30 \mu A \\
& \mathrm{PM}>70^{\circ}
\end{aligned}
$$

Let

$$
P M=90-\tan ^{-1}\left(\frac{G B W}{\omega_{n d}}\right) \rightarrow \omega_{n d} \geq 2.7 G B W
$$

$$
\begin{aligned}
& \omega_{n d}=3 \times G B W==\frac{g_{m 2} C_{c}}{C_{p}\left(C_{c}+C_{L}\right)} \rightarrow \frac{g_{m 2}}{g_{m 1}}=0.3 \\
& \text { Then }
\end{aligned}
$$

$$
g_{m 2}=0.3 g_{m 1} \cong 52 \mu S \rightarrow I_{p, 2}=0.3 I_{p, 0}
$$

$\checkmark$ Let's use $g_{\mathrm{m} 2}=6 \mathrm{gm} 1$ like the miller Opamp to make a comparison between the capacitive driving capability.
$\checkmark$ For the same capacitive load driving capability, the second stage will consume less current making it suitable for low power applications

## Design Example - Improved Compensation



## Design Example - Improved Compensation

- Capacitive load driving capability

- $\quad \mathrm{PM}>70^{\circ}$ for $\mathrm{C}_{\mathrm{L}}<100 \mathrm{pF}$.


## Design Example - Improved Compensation

- Summary of Simulation results

| Parameter | Spec | Miller <br> Compensation | Improved <br> Compensation |
| :---: | :---: | :---: | :---: |
| GBW | $>5 \mathrm{MHz}$ | 5.5 MHz | 6 MHz |
| PM | $>70^{\circ}$ | $75^{\circ}$ | $87.6^{\circ}$ |
| $\mathrm{SR}^{+}$ | $>2 \mathrm{~V} / \mu \mathrm{s}$ | $2.75 \mathrm{~V} / \mu \mathrm{s}$ | $3 \mathrm{~V} / \mu \mathrm{s}$ |
| SR $^{-}$ | $>2 \mathrm{~V} / \mu \mathrm{s}$ | $3 \mathrm{~V} / \mu \mathrm{s}$ | $3.15 \mathrm{~V} / \mu \mathrm{s}$ |
| PSR $^{-}$ | - | -65.6 dB <br> At $(0-3.1 \mathrm{kHz})$ | -51.9 dB <br> PSR $^{+}$ <br> DC gain |
| - | $-975.4 \mathrm{kHz})$ |  |  |
| At $(0-44 \mathrm{kHz})$ | At $(0-538.9 \mathrm{~dB}$ |  |  |
| Current <br> consumption | - | 64.5 dB | 51.3 dB |
| Capacitive load <br> driving capability | - | $80 \mu \mathrm{~A}$ | $110 \mu \mathrm{~A}$ |

Using another current buffer Op Amp topology.


Two-Stage amplifier with Current Buffer compensation scheme.

- Improve SR at the expense of power consumption.

Differential Output Two Stage Amp with a capacitor compensation with a current Buffer ( Common Gate)


## Differential mode half circuit of previous topology



| Element | Fig. 1(a) |
| :---: | :---: |
| $R_{o A}$ | $r_{o 1} \\| r_{o 3}$ |
| $C_{A}$ | $C_{g s 5}+C_{d b 1}+C_{d b 3}+C_{d b 7}$ |
| $R_{o B}$ | $\infty^{*}$ |
| $C_{B}$ | $C_{g s 7}+C_{s b 7} * *$ |
| $R_{L} * * *$ | $r_{o 5}$ |
| $C_{L} * * * *$ | $C_{d b 5}$ |

Note that this and previous structure are fully differential but this approach could be used for single output topologies.

## Compensation using a current buffer ( current gain)



Note that the current-mirror introduces an extra inversion which must be taken into consideration for the single ended version.
P.J. Hurst, Lewis, S.H. ; Keane, J.P. ; Aram, F. ; Dyer, K.C.
" Miller compensation using current buffers in fully differential CMOS two-stage operational amplifiers" IEEE Transactions on Circuits and Systems I, Volume: 51 , Issue: 2, Feb. 2004

| Element |  |
| :---: | :---: |
| $R_{o A}$ | $r_{o 1}\left\\|r_{o 3}\right\\| r_{o l 1}$ |
| $C_{A}$ | $C_{g s 5}+C_{d b 1}+C_{d b 3}+C_{d b 11}$ |
| $R_{o B}$ | $r_{o 9} *$ |
| $C_{B}$ | $C_{g s 9}+C_{g s 11}+C_{d b 9} * *$ |
| $R_{L} * * *$ | $r_{o 5}$ |
| $C_{L} * * * *$ | $C_{d b 5}$ |

$$
z \approx-\frac{g_{m 11}}{C_{B}+C_{c}} .
$$

Besides the above zero the amp has three poles

## Elements of Current-Mirror Cc compensated

Note that the common-gate and current mirror topologies under ideal case are almost identical, however in practice the one using current-mirrors is more power hungry and has a larger parasitic capacitance $C B$


- Roots close to the $\mathrm{j} \omega$ axis for uncompensated

- Potentially unstable for some values of $\mathrm{C}_{\mathrm{L}}$
$\mathrm{I}_{\text {bias }}=\mathrm{C}_{\mathrm{L}} \mathrm{S}_{\mathrm{R}} * 2.5$
- Improved output stage optimal bias of $\mathrm{Q}_{6}$ and $\mathrm{Q}_{7}$
- No significant change of pole locations.
$\mathrm{A}_{\mathrm{v}}(0)->+$
$A_{v}(\omega)->-$

Pole splitting $=>$ one dominant pole

$\mathrm{z}_{1}$ Phase deteriorates phase margin
The good and the bad news

Two possible solutions to cancel $\mathrm{z}_{1}$ and keeping $\mathrm{s}_{\mathrm{p} 2}>\omega_{\mathrm{t}}=\mathrm{GBW}$ and $\mathrm{s}_{\mathrm{p} 1}$ small


Internally Compensated
with $\mathrm{R}_{\mathrm{C}} \mathrm{C}_{\mathrm{C}}$


Internally Compensated with unity gain buffer

$$
\left(\mathrm{Q}_{10}, \mathrm{Q}_{11}\right)
$$

## Operational Amplifier (conventional) Architectures.

Reader.- See the internally Op Amp compensated with current gain buffer in previous pages

## Folded Cascode Op Amp

$\square$ Compared to two-stage Op Amp, folded cascode Op Amp has:

- Improved input common-mode range (ICMR)
- Improved power supply rejection (PSR)
- Push-pull output stage
- Self compensation


Folded-cascode Op Amp broken into stages [Allen]

Folded Cascode OpAmp

$\square$ The extended ICMR is achieved
$\square$ The bias currents I4 and I5 should be designed such that I6 and I7 never goes to zero (i.e. $I_{4,5}=1.2 I_{3} \rightarrow 1.5 I_{3}$ )
$\square$ Poor noise performance: In addition to the input transistors, transistors $\mathrm{M}_{4,5}$ and $\mathrm{M}_{10,11}$ generate significant current noise

## Small Signal Analysis


$\mathrm{R}_{\mathrm{A}}$ and $\mathrm{R}_{\mathrm{B}}$ are the resistances looking into the sources of $\mathrm{M}_{6}$ and $\mathrm{M}_{7}$

$$
R_{A}=\frac{r_{d s 6}+1 / g_{m 10}}{1+g_{m 6} r_{d s 6}} \approx \frac{1}{g_{m 6}} \text { and } R_{B}=\frac{r_{d s 7}+R_{I I}}{1+g_{m 7} r_{d s 7}} \approx \frac{R_{I I}}{g_{m 7} r_{d s 7}} \text { where } R_{I I}=g_{m 9} r_{d s 9} r_{d s 11}
$$

The currents $i_{7}$ and $i_{10}$ is expressed as

$$
\begin{gathered}
i_{7}=\frac{g_{m 2}\left(r_{d s 2} \| r_{d s 5}\right)}{R_{B}+\left(r_{d s 2} \| r_{d s 5}\right)} \frac{v_{i n}}{2}=\frac{g_{m 2}}{k+1} \frac{v_{i n}}{2} \text { where } k=\frac{R_{B}}{r_{d s 2} \| r_{d s 5}} \\
i_{10}=-\frac{g_{m 1}\left(r_{d s 1} \| r_{d s 4}\right.}{R_{A}+\left(r_{d s 1} \| r_{d s 4}\right)} \frac{v_{i n}}{2} \approx-g_{m 1} \frac{v_{i n}}{2}
\end{gathered}
$$

Thus, the transfer function can be found as follows

$$
\frac{v_{o u t}}{v_{\text {in }}}=\left(\frac{g_{m 1}}{2}+\frac{g_{m 2}}{2(k+1)}\right) R_{\text {out }}=\left(\frac{2+k}{2+2 k}\right) g_{m 1} R_{\text {out }}
$$

Where

$$
R_{o u t}=g_{m 9} r_{d s 9} r_{d s 11} \| g_{m 7} r_{d s 7}\left(r_{d s 2} \| r_{d s 5}\right)
$$

Where $k$ is the low-frequency unbalance factor

## Frequency Response

The frequency response is dominated primarily by the output pole due to the high output impedance

$$
P_{\text {out }}=\frac{-1}{R_{\text {out }} C_{\text {out }}}
$$

$\square$ In order to have sufficient phase margin, all other pole should be located will above the GBW

Pole at source of $\mathrm{M}_{6}$ (Folding node)

$$
\begin{aligned}
& P_{A}=-\frac{1}{R_{A}\left(C_{g s}+2 C_{b d}\right)} \approx-\frac{g_{m 6}}{C_{g s}+2 C_{b d}} \\
& P_{B}=-\frac{1}{R_{B}\left(C_{g s}+2 C_{b d}\right)} \approx-\frac{g_{m 7}}{C_{g s}+2 C_{b d}} \\
& P_{6}=-\frac{g_{m 10}}{2 C_{g s}+2 C_{b d}} \\
& P_{8}=-\frac{g_{m 8} r_{d s 8} g_{m 10}}{C_{g s}+C_{b d}} \\
& P_{9}=-\frac{g_{m 9}}{C_{g s}+C_{b d}}
\end{aligned}
$$

Pole at source of $\mathrm{M}_{7}$ (Folding node)
Pole at drain of $\mathrm{M}_{6}$
Pole at source of $\mathrm{M}_{8}$
Pole at source of $\mathrm{M}_{9}$

## $\square$ Remarks:

We assumed $R_{B} \approx 1 / g_{m 7}$ because at high frequency, where this pole has influence, $C_{o u t}$ shunts the drain of $M_{7}$ to ground.

## Power Supply Rejection

$\square$ The following model is used to calculate the negative PSR

- The gate, source and drain of $\mathrm{M}_{11}$ varies with $\mathrm{V}_{\mathrm{SS}}$
- The gate, source of $\mathrm{M}_{9}$ varies with $\mathrm{V}_{\mathrm{ss}}$


$$
\frac{V_{\text {out }}}{V_{s s}}=\frac{s C_{\text {gd } 9} R_{\text {out }}}{s C_{\text {out }} R_{\text {out }}+1}
$$

$\square P S R R^{-}$can be calculated

$$
P S R R^{-}=\frac{A_{v}}{\left|V_{\text {out }} / V_{s s}\right|}
$$


[Allen]

## Power Supply Rejection



At low frequency, we assume that other source of $V_{s s}$ injection becomes significant
L Low frequency PSRR- is at least as large as the magnitude of the differential voltage gain $A_{v}$
PSRR ${ }^{+}$can be derived similarly: the primary source of injection is through

## Slew Rate



$$
S R^{+}=S R^{-}=\frac{I_{3}}{C_{L}}
$$

The bias currents $I_{4,5}$ should be designed such that $I_{6,7}$ never goes to zero

$$
I_{4,5}=1.2 I_{3} \rightarrow 1.5 I_{5}
$$

## Maximum Available Output Swing



The output common mode level $V_{o c m}$ is often dictated by the circuit that interface with the amplifier (e.g. $V_{o c m}=V_{D D} / 2$ )

## Noise Analysis

$\square$ The noise current of $\mathrm{M}_{1}, \mathrm{M}_{4}$ and $\mathrm{M}_{10}$ goes directly to the output
$\square$ At low and medium frequencies, noise contribution of the cascode transistors ( $\mathrm{M}_{6}$ and $\mathrm{M}_{8}$ ) can be neglected
$\square$ Total output noise current becomes

$$
\overline{i_{o u t}^{2}}=8 K T \gamma\left(g_{m 1}+g_{m 4}+g_{m 10}\right)
$$

$\square$ Input referred noise density

$$
\overline{v_{n, i n}^{2}}=\frac{8 K T \gamma}{g_{m 1}}\left(1+\frac{g_{m 4}}{g_{m 1}}+\frac{g_{m 10}}{g_{m 1}}\right)
$$



## Folded Cascode Op Amp Design Procedure

Design approach for the folded cascode Op Amp using long-channel model

| Step | Relationship | Design Equation/Constraint | Comments |
| :---: | :---: | :---: | :---: |
| 1 | Slew Rate | $I_{3}=S R \cdot C_{L}$ |  |
| 2 | Bias currents in output cascodes | $I_{4}=I_{5}=1.2 I_{3}$ to $1.5 I_{3}$ | Avoid zero current in cascodes |
| 3 | Maximum output voltage, <br> $v_{\text {out }}$ (max) | $S_{5}=\frac{2 I_{5}}{K_{P} V_{S D 5^{2}}^{2}}, S_{7}=\frac{2 I_{7}}{K_{P} V_{S D 7^{2}}^{2}},\left(\mathrm{~S}_{4}=\mathrm{S}_{5} \text { and } \mathrm{S}_{6}=\mathrm{S}_{7}\right)$ | $\begin{aligned} & V_{S D 5}(\mathrm{sat})=V_{S D 7}(\mathrm{sat}) \\ & =0.5\left[V_{D D^{-}} V_{\text {out }}(\mathrm{max})\right] \end{aligned}$ |
| 4 | Minimum output voltage, <br> $v_{\text {out }}(\mathrm{min})$ | $S_{11}=\frac{2 I_{11}}{K_{N} V_{D S 11^{2}}}, S_{9}=\frac{2 I_{9}}{K_{N} V_{D S 9^{2}}},\left(\mathrm{~S}_{10}=\mathrm{S}_{11} \text { and } \mathrm{S}_{8}=\mathrm{S}_{9}\right)$ | $\begin{aligned} & V_{D S 9}(\mathrm{sat})=V_{D S 11}(\mathrm{sat}) \\ & =0.5\left[V_{\text {out }}(\mathrm{min})-V_{S S}\right] \end{aligned}$ |
| 5 | $G B=\frac{g_{m 1}}{C_{L}}$ | $S_{1}=S_{2}=\frac{g_{m 1^{2}}}{K_{N} I_{3}}=\frac{G B^{2} C_{L}^{2}}{K_{N} I_{3}}$ |  |
| 6 | Minimum input CM | $\mathrm{S}_{3}=\frac{2 I_{3}}{K_{N}\left(V_{\text {in }}(\mathrm{min})-V_{S S}-\sqrt{\left(I_{3} / K_{N} \mathrm{~S}_{1}\right)}-V_{T 1}\right)^{2}}$ |  |
| 7 | Maximum input CM | $\mathrm{S}_{4}=\mathrm{S}_{5}=\frac{2 I_{4}}{K_{P}\left(V_{D D^{-}} V_{\text {in }}(\max )+V_{T 1}\right)}{ }^{2}$ | $\mathrm{S}_{4}$ and $\mathrm{S}_{5}$ must meet or exceed value in step 3 |
| 8 | Differential Voltage Gain | $\frac{v_{\text {out }}}{v_{\text {in }}}=\left(\frac{g_{m 1}}{2}+\frac{g_{m 2}}{2(1+k)}\right) R_{\text {out }}=\left(\frac{2+k}{2+2 k}\right) g_{m I} R_{\text {out }}$ | $k=\frac{R_{I I}\left(g_{d s 2}+g_{d s 4}\right)}{g_{m 7^{r}} d s 7}$ |
| 9 | Power dissipation | $P_{\text {diss }}=\left(V_{D D^{-}} V_{S S}\right)\left(I_{3}+I_{10}+I_{11}\right)$ |  |

## Design Example

$\square$ Design a folded cascode Op Amp to comply with the following specifications using $0.18 \mu \mathrm{~m}$ CMOS technology

| Parameter | Spec |
| :--- | :---: |
| Slew rate | $>10 \mathrm{~V} / \mu \mathrm{s}$ |
| Load Capacitor | 10 pF |
| Power Supply | $\pm 1 \mathrm{~V}$ |
| Max/Min Output Voltage | $\pm 0.5 \mathrm{~V}$ |
| GBW | $>10 \mathrm{MHz}$ |
| Min Input CM Voltage | -0.3 V |
| Max Input CM Voltage | 1 V |
| Differential Voltage Gain | $>60 \mathrm{~dB}$ |
| Power Dissipation | $<2 \mathrm{~mW}$ |

## Design Example (Cont.)

## $\square$ Solution:

$>$ From the value of the slew rate we can get $\mathrm{I}_{3}$
$\mathrm{I}_{3}=\mathrm{SR} \times \mathrm{C}_{\mathrm{L}}>\left(10 \times 10^{6}\right)\left(10 \times 10^{-12}\right) \rightarrow \mathrm{I}_{3} \geq 100 \mu \mathrm{~A}$
Select $\mathrm{I}_{3}=120 \mu \mathrm{~A}$
$>I_{4,5}$ will be designed such that $I_{6,7}$ never goes to zero
$\mathrm{I}_{4}=\mathrm{I}_{5}=1.2 \mathrm{I}_{3}$ to $1.5 \mathrm{I}_{3}$
Select $\mathrm{I}_{4}=\mathrm{I}_{5}=1.25 \mathrm{I}_{3}=150 \mu \mathrm{~A}$

$>$ Knowing $I_{4}$ and $I_{3}$, we can get the quiescent, min, and max values of $I_{6,7}{ }^{\frac{1}{=}}$
$I_{6, Q}=I_{7, Q}=I_{4}-0.5 I_{3}=90 \mu \mathrm{~A}$
$I_{6(\text { min })}=I_{7(\text { min })}=I_{4}-I_{3}=20 \mu \mathrm{~A}$
$I_{6(\max )}=I_{7(\max )}=I_{4}=150 \mu \mathrm{~A}$
$>$ From the min and maximum output voltages we can get overdrive voltage of transistors $M_{4-11}$

$$
\begin{aligned}
& \left.V_{\text {SDsat }(4-7)}\right|_{\max }=0.5\left(V_{D D}-V_{\text {out }(\max )}\right)=0.25 \mathrm{~V} \\
& \left.V_{\text {DSsat }(8-11)}\right|_{\max }=0.5\left(V_{\text {out }(\min )}-V_{S S}\right)=0.25 \mathrm{~V}
\end{aligned}
$$

## Design Example (Cont.)

> The value of $G B$ gives $g_{m 1,2}$

$$
g_{m 1,2}=G B \times C_{L} \geq 628.3 \mu A / V
$$

Thus, choose $g_{m 1,2}=700 \mu \mathrm{~A} / \mathrm{V}$
From $g_{m 1,2}$ and $I_{1,2}$, we can obtain $V_{D S s a t(1,2)}$

$$
V_{D S s a t(1,2)}=\frac{2 I_{1}}{g_{m 1}}=\frac{I_{3}}{g_{m 1}}=0.17 \mathrm{~V}
$$

- The minimum input common mode voltage defines $V_{D S s a t 3}$

$V_{\text {icm(min) }}=V_{S S}+V_{D S s a t(3)}+V_{T n}+V_{D S s a t(1)}$
Thus, $V_{D S s a t(3)}=0.13 \mu A$ for $V_{T n}=0.4 \mathrm{~V}$
$>$ We need to check that the maximum input common mode voltage is satisfied $V_{i c m(\max )}=V_{D D}-V_{S D \operatorname{sat}(4)}+V_{T n}=1.15 \mathrm{~V} \rightarrow$ Meets the spec


## Design Example (Cont.)

$\square$ Now, we have the bias currents $I_{D}$ and overdrive voltage $V_{D S \text { sat }}$ of all the transistors. Thus, we can obtain $W / L$ of all the transistors from the ACM model or square-law model if long-channel transistors are used.
$\square$ The channel length of the transistors should be chosen to satisfy the specified voltage gain.
$\square$ The current flowing in transistors $M_{6-11}$ can have any value from $20 \mu A$ to $150 \mu A$ depending on the amplitude and polarity of the differential input voltage. Therefore, they should be sized such that the worst case $V_{D S s a t}$ of each transistor meets the specified limits on the output voltages.
$\square$ Bias voltages of the cascode transistors $V_{P B 2}$ and $V_{N B 2}$ are chosen such that $V_{P B 2}$

## Simulation Results

## $\square$ DC operating point

| Transistor | $\boldsymbol{W} / \boldsymbol{L}$ | $\boldsymbol{I}_{\boldsymbol{D}}(\boldsymbol{\mu} \boldsymbol{A})$ | $\boldsymbol{V}_{\text {DSsat }}$ |
| :---: | :---: | :---: | :---: |
| $M_{1,2}$ | $18 / 1$ | 120 | 0.13 |
| $M_{3}$ | $24 / 1$ | 60 | 0.16 |
| $M_{4,5}$ | $72 / 1$ | 150 | 0.23 |
| $M_{6,7}$ | $72 / 1$ | 90 | 0.23 |
| $M_{8,9}$ | $12 / 1$ | 90 | 0.24 |
| $M_{10,11}$ | $12 / 1$ | 90 | 0.24 |

## $\square$ Input common-mode range




Minimum input common mode voltage is 0.28 V

## Simulation Results

## $\square$ Output Swing



The gain is perfectly linear for $-0.5 \leq V_{\text {out }} \leq 0.5$

## $\square$ Open loop response



Open loop response testbench


Simulation Results
$\square$ Slew Rate



## Simulation Results

$\square$ PSRR


PSRR $^{+}$testbench



PSRR ${ }^{-}$testbench


## Summary of Results

$\square$ The following simulation results for $C_{L}=10 p F, V_{D D}=1 \mathrm{~V}$ and $V_{S S}=-1 V$

| Parameter | Spec | Simulation |
| :--- | :---: | :---: |
| SR $^{+}$ | $>10 \mathrm{~V} / \mu \mathrm{s}$ | $11.3 \mathrm{~V} / \mu \mathrm{s}$ |
| SR $^{-}$ | $>10 \mathrm{~V} / \mu \mathrm{s}$ | $11.18 \mathrm{~V} / \mu \mathrm{s}$ |
| Max/Min Output Voltage | $\pm 0.5 \mathrm{~V}$ | $-0.65 \rightarrow 0.61 \mathrm{~V}$ |
| GBW | $>10 \mathrm{MHz}$ | 10.7 MHz |
| Min Input CM Voltage | -0.3 V | -0.28 V |
| Max Input CM Voltage | 1 V | 1 V |
| Differential Voltage Gain | $>60 \mathrm{~dB}$ | 62 dB |
| PSRR $^{+}$ | - | 65.64 dB |
| PSRR $^{-}$ | - | 75.86 dB |
| Power Dissipation | $<2 \mathrm{~mW}$ | $840 \mu \mathrm{~W}$ |
|  |  |  |

## Techniques for Wideband Amplifiers

## Focus the improvement in the load of the differential pair



Conventional

## Current Mirror at the output load




Low Frequency Behavior

Behavior


Frequency Dependent Current Mirror (FDCM)

$$
\mathrm{C}_{\mathrm{F}} \gg \mathrm{Cgs}
$$

$0.1 \mathrm{~K}<\mathrm{R}<1 \mathrm{~K}$

An example of its use:


## Wideband Amplifier with Feedforward Technique

-What is the optimal value of R1 as a function og GmP3 ?

- $\mathrm{C}_{\mathrm{F} 1}$ by passes two current mirrors.
- $\mathrm{C}_{\mathrm{F} 2}$ is fed forward to the input of another FDCM and signal is amplified.

Next, we discuss different families of wideband reported in the literature.


- An alternative is to connect $\mathrm{C}_{\mathrm{F}}$ instead to nodes B to nodes A
F. Centurelli et al, "A Bootstrap Technique for Wideband Amplifiers," IEEE Trans. on Circuits And Systesm - I, Vol. 49, No. 10, pp. 1474-1480, October 2002


## FOLDED-CASCODE WIDEBAND AMPLIFIER (See page 11 for cascode)




FC with Capacitive Feedforward


Differential Wideband Amplifier

E.K.F. Lee, " Low-Voltage Opamp Design and Differential Difference Amplifier Design Using Linear Transconductor with Resistor Input


Fig 3 VCVS Amplifier: Op Amp


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